

Docket No.: F03-354-USDiv  
FUJIT.044DIV



*gtm*

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re patent application of

Hisaki KATO, et al.

Serial No.: 10/634,836

Group Art Unit: 2822

Filed: August 6, 2003

Examiner: Keisha L. Rose

For: LIGHT-EMITTING SEMICONDUCTOR DEVICE USING GALLIUM  
NITRIDE COMPOUND SEMICONDUCTOR

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicants' duty of disclosure under 37 CFR §1.56, applicants respectfully bring the following documents, cited in the Japanese Office Action and listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. An English translation of the Japanese Office Action is enclosed. Copies of the listed documents are also provided herewith for the convenience of the Examiner.

In compliance with the requirements of 37 CFR §1.98(a)(3), as a concise statement of relevance, as it is presently understood by the individual designated in 35 U.S.C. §1.56(c) most knowledgeable about the content of the information, the undersigned attorney of record submits a translation of portions of an official action by a foreign examiner in which the reference was cited. The relevance to the pending U.S. patent application is that the reference was cited in a foreign patent application on the same subject matter. However, no independent analysis of the reference, the accuracy of the statement of the foreign examiner or the claims of the foreign application under the laws of that country or the United States relative to the subject matter claimed in the present application has been made, the present understanding of the contents thereof by the undersigned being based on the translation of the foreign examiner's comments submitted herewith.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicants are aware.

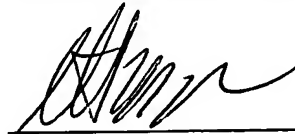
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I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of that item by a foreign patent office in a counterpart foreign application, which occurred not more than three months prior to the filing of this statement.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



\_\_\_\_\_  
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**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional)  
**F03-354-USDiv**

Application Number  
**10/634,836**

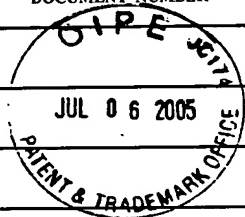
Applicant(s)  
**Hisaki KATO, et al.**

Filing Date  
**August 6, 2003**

Group Art Unit  
**2822**

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE



**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		H7-7182	01/10/99	Japan			ABS	

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

Japanese Office Action, dated May 24, 2005, with partial English translation

NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.